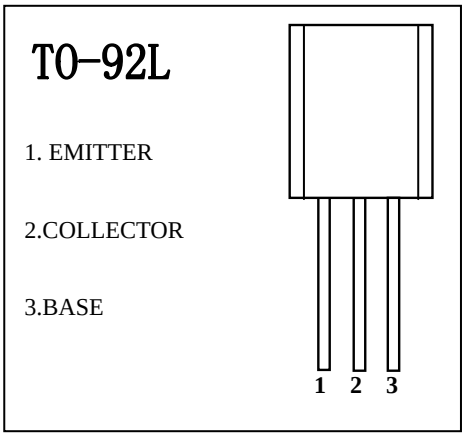
深圳市晶泰源电子有限公司

2SB647 TRANSISTOR(PNP)



FEATURES

- Excellent linearity or Current Gain
- Low saturation voltage
- Complementary to 2SD667

MAXIMUM RATINGS(TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Colleator-Base Voltage	-120	V
VCEO	Colleator-Emitter Voltage	-80	V
VEBO	Emitter-Base Voltage	-5	V
IC	Colleator Current-Continuous	-1.0	A
PC	Coueator Power Dissipature	0.9	W
TJ	Junction Temperature	150	℃
Tatg	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS(Tamb=25℃ unless otherwise specjfied):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-120			V
Collector-emittre breakdown' voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_C=-1mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-120V, I_E=0			-0.5	μA
Collector cut-off current	I_{CEO}	Vce=-80V, I_B=0			-1.0	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	H_{FE}	Vce=-5V, Ic=-1mA	60		320	
Collector-emittre saturation voltage	VCE(sat)	I_C=-500mA, I_B=-50mA			-1.0	V
Base-emittre saturation voltage	VBE(sat)	I_C=-500mA, I_B=-50mA			-1.5	V
Gain Bandwidth Product	fT	V_{CE}=-2V, I_C=500mAz		140		MHz

深圳市晶泰源电子有限公司
电话：0755-83211536 传真：0755-83206326
深圳市福田区华强北路华强广场C座11C